

# IXTH200N085T

Request a Quote

### **IXTH200N085T Information**

	Part Number	IXTH200N085T
www.heltener.com	Manufacturer	IXYS
	Category	Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single
	Description	MOSFET N-CH 85V 200A TO-247
	Package	TO-247-3
		For the pricing/inventory/lead time, please contact
For Reference Only		us Website: https://www.heisener.com E-mail: salesdept@heisener.com

# **Certified Quality**

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.



# **IXTH200N085T Specifications**

ManufacturerIXYSCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-247-3SeriesTrenchMY?FET TypeN-ChannelTecnhologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)85VCurrent - Continuous Drain (Id) @ 25°C200A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250µAGate Charge (Qg) (Max) @ Vgs152nC @ 10VInput Capacitance (Ciss) (Max) @ Vds7600pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)480W (Tc)Rds On (Max) @ Id, Vgs5 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247 (XTH)		
CategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-247-3SeriesTrenchMV?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)85VCurrent - Continuous Drain (Id) @ 25°C200A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250µAGate Charge (Qg) (Max) @ Vgs152nC @ 10VInput Capacitance (Ciss) (Max) @ Vds260VFET Feature-Power Dissipation (Max)480W (Tc)Rds On (Max) @ Id, Vgs5 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247 (IXTH)Package / CaseTO-247-3	Manufacturer Part Number	IXTH200N085T
PackageTransistors - FETs, MOSFETs - SinglePackageTO-247-3SeriesTrenchMV?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)85VCurrent - Continuous Drain (Id) @ 25°C200A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250µAGate Charge (Qg) (Max) @ Vgs152nC @ 10VInput Capacitance (Ciss) (Max) @ Vds7600pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)480W (Tc)Rds On (Max) @ Id, Vgs5 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247 (IXTH)Package / CaseTO-247.3	Manufacturer	IXYS
PackageTO-247-3SeriesTrenchMV?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)85VCurrent - Continuous Drain (Id) @ 25°C200A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250µAGate Charge (Qg) (Max) @ Vds152nC @ 10VInput Capacitance (Ciss) (Max) @ Vds7600pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)480W (Tc)Rds On (Max) @ Id, Vgs5 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247 (IXTH)Package / CaseTO-247-3	Category	Discrete Semiconductor Products
Series TrenchMV?   FET Type N-Channel   Technology MOSFET (Metal Oxide)   Drain to Source Voltage (Vdss) 85V   Current - Continuous Drain (Id) @ 25°C 200A (Tc)   Drive Voltage (Max Rds On, Min Rds On) 10V   Vgs(th) (Max) @ Id 4V @ 250µA   Gate Charge (Qg) (Max) @ Vgs 152nC @ 10V   Input Capacitance (Ciss) (Max) @ Vds 7600pF @ 25V   Vgs (Max) ±20V   FET Feature -   Power Dissipation (Max) 480W (Tc)   Rds On (Max) @ Id, Vgs 5 mOhm @ 25A, 10V   Operating Temperature -55°C ~ 175°C (TJ)   Mounting Type Through Hole   Supplier Device Package TO-247 (IXTH)   Package / Case TO-247-3		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)85VCurrent - Continuous Drain (Id) @ 25°C200A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250µAGate Charge (Qg) (Max) @ Vgs152nC @ 10VInput Capacitance (Ciss) (Max) @ Vds7600pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)480W (Tc)Rds On (Max) @ Id, Vgs5mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247 (IXTH)Package / CaseTO-247-3	Package	TO-247-3
A MOSFET (Metal Oxide)   Technology MOSFET (Metal Oxide)   Drain to Source Voltage (Vdss) 85V   Current - Continuous Drain (Id) @ 25°C 200A (Tc)   Drive Voltage (Max Rds On, Min Rds On) 10V   Vgs(th) (Max) @ Id 4V @ 250µA   Gate Charge (Qg) (Max) @ Vgs 152nC @ 10V   Input Capacitance (Ciss) (Max) @ Vds 7600pF @ 25V   Vgs (Max) ±20V   FET Feature -   Power Dissipation (Max) 480W (Tc)   Rds On (Max) @ Id, Vgs 5 mOhm @ 25A, 10V   Operating Temperature -55°C ~ 175°C (TJ)   Mounting Type Through Hole   Supplier Device Package TO-247 (IXTH)   Package / Case TO-247-3	Series	TrenchMV?
Drain to Source Voltage (Vdss)85VCurrent - Continuous Drain (Id) @ 25°C200A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250µAGate Charge (Qg) (Max) @ Vgs152nC @ 10VInput Capacitance (Ciss) (Max) @ Vds7600pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)480W (Tc)Rds On (Max) @ Id, Vgs5 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247 (IXTH)Package / CaseTO-247-3	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°С 200A (Tc)   Drive Voltage (Max Rds On, Min Rds On) 10V   Vgs(th) (Max) @ Id 4V @ 250µA   Gate Charge (Qg) (Max) @ Vgs 152nC @ 10V   Input Capacitance (Ciss) (Max) @ Vds 7600pF @ 25V   Vgs (Max) ±20V   FET Feature -   Power Dissipation (Max) 480W (Tc)   Rds On (Max) @ Id, Vgs 5 mOhm @ 25A, 10V   Operating Temperature -55°C ~ 175°C (TJ)   Mounting Type Through Hole   Supplier Device Package TO-247 (IXTH)   Package / Case TO-247-3	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs152nC @ 10VInput Capacitance (Ciss) (Max) @ Vds7600pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)480W (Tc)Rds On (Max) @ Id, Vgs5 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247 (IXTH)Package / CaseTO-247-3	Drain to Source Voltage (Vdss)	85V
Vgs(th) (Max) @ Id 4V @ 250μA   Gate Charge (Qg) (Max) @ Vgs 152nC @ 10V   Input Capacitance (Ciss) (Max) @ Vds 7600pF @ 25V   Vgs (Max) ±20V   FET Feature -   Power Dissipation (Max) 480W (Tc)   Rds On (Max) @ Id, Vgs 5 mOhm @ 25A, 10V   Operating Temperature -55°C ~ 175°C (TJ)   Mounting Type Through Hole   Supplier Device Package TO-247 (IXTH)   Package / Case TO-247-3	Current - Continuous Drain (Id) @ 25°C	200A (Tc)
Gate Charge (Qg) (Max) @ Vgs152nC @ 10VInput Capacitance (Ciss) (Max) @ Vds7600pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)480W (Tc)Rds On (Max) @ Id, Vgs5 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247 (IXTH)Package / CaseTO-247-3	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds7600pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)480W (Tc)Rds On (Max) @ Id, Vgs5 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247 (IXTH)Package / CaseTO-247-3	Vgs(th) (Max) @ Id	4V @ 250µA
Ygs (Max)±20VFET Feature-Power Dissipation (Max)480W (Tc)Rds On (Max) @ Id, Vgs5 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247 (IXTH)Package / CaseTO-247-3	Gate Charge (Qg) (Max) @ Vgs	152nC @ 10V
FET Feature-Power Dissipation (Max)480W (Tc)Rds On (Max) @ Id, Vgs5 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247 (IXTH)Package / CaseTO-247-3	Input Capacitance (Ciss) (Max) @ Vds	7600pF @ 25V
Power Dissipation (Max)480W (Tc)Rds On (Max) @ Id, Vgs5 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247 (IXTH)Package / CaseTO-247-3	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs5 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247 (IXTH)Package / CaseTO-247-3	FET Feature	-
Operating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247 (IXTH)Package / CaseTO-247-3	Power Dissipation (Max)	480W (Tc)
Mounting TypeThrough HoleSupplier Device PackageTO-247 (IXTH)Package / CaseTO-247-3	Rds On (Max) @ Id, Vgs	5 mOhm @ 25A, 10V
Supplier Device PackageTO-247 (IXTH)Package / CaseTO-247-3	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-247-3	Mounting Type	Through Hole
	Supplier Device Package	TO-247 (IXTH)
Report errors?	Package / Case	TO-247-3
		Report errors?

#### **IXTH200N085T** Guarantees



Quality Guarantees

We provide 90 days warranty. \* If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.

# SERVICE

#### **Service Guarantees**

We guarantee 100% customer satisfaction. Our experienced sales team and tech support team back our services to satisfy all our customers.

#### IXTH200N085T Payment Methods



# IXTH200N085T Shipping Methods



If you have any question about IXTH200N085T, please do not hesitate to contact us! Website: https://www.heisener.com E-mail: salesdept@heisener.com